## Typical Applications

## - CATV Distribution Amplifiers

- Cable Modems
- Broadband Gain Blocks


## - Laser Diode Driver

- Return Channel Amplifier
- Base Stations


## Product Description

The RF2360 is a general purpose, low-cost, high-linearity RF amplifier IC. The device is manufactured on a Gallium Arsenide process and is featured in an SOP-16 batwing package. It has been designed for use as an easily cascadable $75 \Omega$ gain block with a Noise Figure of less than 2 dB . Gain flatness better than 0.5 dB from 5 MHz to 1000 MHz , and high linearity make this part ideal for cable TV applications. Other applications include IF and RF amplification in wireless voice and data communication products operating in frequency bands up to 1000 MHz . The device is self-contained with $75 \Omega$ input and output impedances providing less than 2:1 VSWR matching. For higher input and output return losses, see the evaluation schematic.

Optimum Technology Matching ${ }^{\circledR}$ AppliedSi BJTGaAs HBTGaAs MESFETSi Bi-CMOSSiGe HBTSi CMOS


Functional Block Diagram


Package Style: Standard Batwing

## Features

- 5 MHz to 1500 MHz Operation
- Internally Matched Input and Output
- 20dB Small Signal Gain
- 1.2 dB Noise Figure
- +24dBm Output Power
- Single 6V to 9V Positive Power Supply

| Ordering |  |
| :--- | :--- |
| Information |  |
| RF2360 | Linear General Purpose Amplifier |
| RF2360 PCBA | Fully Assembled Evaluation Board $50 \Omega$ |
| RF2360 411 | Fully Assembled Evaluation Board 75H |
| RF2360 412 | Fully Assembled Evaluation Board 75L |
| RF Micro Devices, Inc. Tel (336) 6641233 <br> 7625 Thorndike Road Fax (336) 664 0454 <br> Greensboro, NC 27409, USA http://www.rfmd.com |  |

Absolute Maximum Ratings

| Parameter | Rating | Unit |
| :--- | :---: | :---: |
| Device Current | 175 | mA |
| Device Voltage | 9 | V |
| Input RF Power | +13 | dBm |
| Output Load VSWR | $20: 1$ |  |
| Ambient Operating Temperature | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature | -40 to +150 | ${ }^{\circ} \mathrm{C}$ |

RF Micro Devices believes the furnished information is correct and accurate at the time of this printing. However, RF Micro Devices reserves the right to make changes to its products without notice. RF Micro Devices does not assume responsibility for the use of the described product(s).

| Parameter | Specification |  |  | Unit | Condition |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Typ. | Max. |  |  |
| Overall (50 $\Omega$ ) <br> Frequency Range Input VSWR <br> Output VSWR <br> Gain <br> Gain Flatness <br> Noise Figure <br> Noise Figure <br> Output $\mathrm{IP}_{3}$ <br> Output $\mathrm{IP}_{3}$ <br> Output $\mathrm{IP}_{3}$ <br> Output $\mathrm{IP}_{2}$ <br> Output $\mathrm{IP}_{2}$ <br> Output $\mathrm{P}_{1 \mathrm{~dB}}$ <br> Output $\mathrm{P}_{1 \mathrm{~dB}}$ <br> Output $\mathrm{P}_{1 \mathrm{~dB}}$ <br> Reverse Isolation <br> Gain <br> Gain Flatness <br> Noise Figure <br> Noise Figure <br> Output $\mathrm{IP}_{3}$ <br> Output $\mathrm{IP}_{3}$ <br> Output $\mathrm{IP}_{3}$ <br> Output $\mathrm{IP}_{2}$ <br> Output $\mathrm{IP}_{2}$ <br> Output $P_{1 d B}$ <br> Output $P_{1 d B}$ <br> Output $P_{1 \mathrm{~dB}}$ | 5 | $\begin{gathered} 1.6: 1 \\ \\ \text { 1.2:1 } \\ 20 \\ +/-0.9 \\ 1.2 \\ 1.5 \\ 33.7 \\ 37.2 \\ 36.4 \\ 46.3 \\ 44.4 \\ 21 \\ 24 \\ 23.7 \\ 24 \\ \\ 20 \\ \hline+/-0.9 \\ 1.1 \\ 1.5 \\ 34.8 \\ 38.1 \\ 38.7 \\ 44.1 \\ 48.6 \\ 22.5 \\ 25.1 \\ 25.3 \end{gathered}$ | 1500 | dBm <br> dBm <br> dBm <br> dBm <br> dBm <br> dBm <br> dBm <br> dBm <br> dB <br> dB <br> dB <br> dB <br> dB <br> dBm <br> dBm <br> dBm <br> dBm <br> dBm <br> dBm <br> dBm <br> dBm | $\begin{aligned} & \mathrm{T}=25^{\circ} \mathrm{C}, \mathrm{~V}_{\mathrm{DD}}=7 \mathrm{~V}, 50 \Omega \text { System, } \\ & \mathrm{P}_{\mathrm{IN}}=-8 \mathrm{dBm} \end{aligned}$ <br> 3dB Bandwidth <br> Appropriate values for the output DC blocking capacitor and bias inductor are required to maintain this VSWR over the intended operating frequency range. <br> See note for Input VSWR. <br> At 500 MHz <br> 5 MHz to 1000 MHz <br> At 500 MHz <br> From 5 MHz to 1000 MHz <br> At 10 MHz , Delta F1 and F2 $=1 \mathrm{MHz}$ <br> At 500 MHz <br> At 1000 MHz <br> At 100 MHz , Delta F1 and F2 $=156 \mathrm{MHz}$ <br> At 1000 MHz <br> At 10 MHz <br> At 500 MHz <br> At 1000 MHz <br> At 500 MHz $\mathrm{T}=25^{\circ} \mathrm{C}, \mathrm{~V}_{\mathrm{DD}}=9 \mathrm{~V}, \mathrm{P}_{\mathrm{IN}}=-8 \mathrm{dBm}$ <br> At 500 MHz <br> 5 MHz to 1000 MHz <br> At 500 MHz <br> From 5 MHz to 1000 MHz , <br> At 10 MHz , Delta F1 and F2 $=1 \mathrm{MHz}$ <br> At 500 MHz <br> At 1000 MHz <br> At 100 MHz , Delta F1 and F2 $=156 \mathrm{MHz}$ <br> At 1000 MHz <br> At 10 MHz <br> At 500 MHz <br> At 1000 MHz |
| Power Supply <br> Supply Voltage (VD) | 6 | 7 | 9 | V |  |

## Preliminary

RF2360


## RF2360

| Pin | Function | Description | Interface Schematic |
| :---: | :---: | :--- | :--- |
| $\mathbf{1}$ | NC | No connection. This pin should be connected to the ground plane. |  |
| $\mathbf{2}$ | NC | Same as pin 1. |  |
| $\mathbf{3}$ | GND | Ground connection. Keep traces physically short and connect immedi- <br> ately to ground plane for best performance. Each ground pin should <br> have a via to the ground plane. |  |
| $\mathbf{4}$ | GND | Same as pin 3. |  |
| $\mathbf{5}$ | GND | Same as pin 3. |  |
| $\mathbf{6}$ | RF IN | RF input pin. This pin is internally DC blocked. An external DC blocking <br> capacitor is not required. |  |
| $\mathbf{7}$ | NC | Same as pin 1. |  |
| $\mathbf{8}$ | NC | Same as pin 1. |  |
| $\mathbf{9}$ | NC | Same as pin 1. |  |
| $\mathbf{1 0}$ | NC | Same as pin 1. |  |
| $\mathbf{1 1}$ | NC | Same as pin 1. |  |
| $\mathbf{1 2}$ | GND | Same as pin 3. |  |
| $\mathbf{1 3}$ | GND | Same as pin 3. |  |
| $\mathbf{1 4}$ | RF OUT | RF output and bias pin. Because DC is present on this pin, a DC block- <br> ing capacitor, suitable for the frequency of operation, should be used in <br> most applications. For biasing, only an RF choke is needed. |  |
| $\mathbf{1 5}$ |  |  |  |
| $\mathbf{1 6}$ | NC | NC | Same as pin 1. |

## Application Schematic $869-894 \mathrm{MHz}$ Narrow band Operation



## Evaluation Board Schematic - $50 \Omega$

(Download Bill of Materials from www.rfmd.com.)


## Evaluation Board Schematic－ $75 \Omega$ High Frequency （ 50 MHz to 2000 MHz ）



NOTES：
J 1 and J 2 are $75 \Omega \mathrm{~F}$ connectors．

## Evaluation Board Schematic－ $75 \Omega$ Low Frequency

（ 5 MHz to 200 MHz ）


J 1 and J 2 are $75 \Omega$ F connectors．

Evaluation Board Layout - $50 \Omega$<br>Board Size 1.5" x 1.5"<br>Board Thickness 0.031", Board Material FR-4



Evaluation Board Layout - $75 \Omega$ High Frequency ( 50 MHz to 2000 MHz )
Board Size 1.25" x 1.0"
Board Thickness 0.062", Board Material FR-4


Evaluation Board Layout - $75 \Omega$ Low Frequency ( 5 MHz to 200 MHz )



Gain, OIP2 and OIP3 versus Temperature




50 Ohm, 8V - Return Loss


## 75 Ohm, 8V - Return Loss



